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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

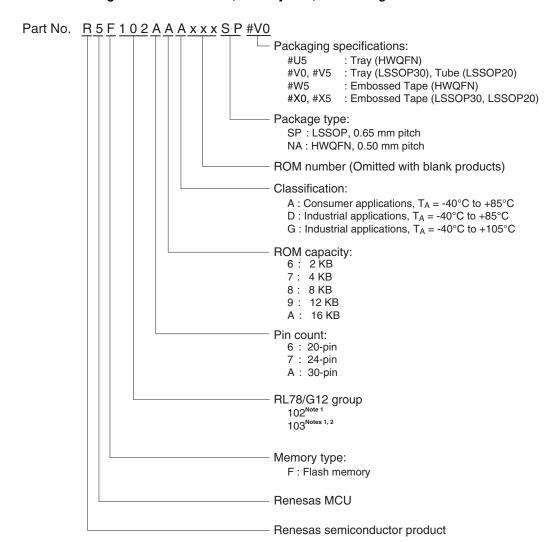
Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	23
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	30-LSSOP (0.240", 6.10mm Width)
Supplier Device Package	30-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f103a8asp-x0

1.2 List of Part Numbers

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Figure 1-1. Part Number, Memory Size, and Package of RL78/G12



- Notes 1. For details about the differences between the R5F102 products and the R5F103 products of RL78/G12, see 1.1 Differences between the R5F102 Products and the R5F103 Products.
 - 2. Products only for "A: Consumer applications ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)" and "D: Industrial applications ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)"

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition		MAX	Unit
High-speed on-chip	T _A = -20 to +85 °C	-1.0	+1.0	%
oscillator oscillation	T _A = -40 to -20 °C	-1.5	+1.5	
frequency accuracy	T _A = +85 to +105 °C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	T _A = -40 to + 85 °C	-5.0	+5.0	%
oscillator oscillation				
frequency accuracy				

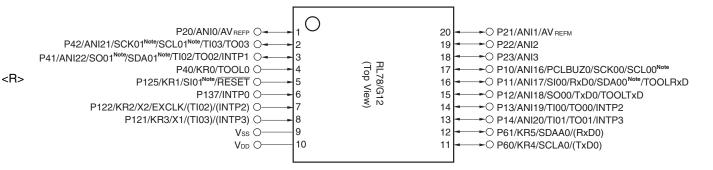
1.3.3 Peripheral Functions

The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

		R5F102	R5F102 product		product	
RL78/G12	20, 24 pin	30 pin product	20, 24 pin	30 pin		
		product		product	product	
Serial interface	UART	1 channel	3 channels	1 channel		
	CSI	2 channels	3 channels	1 channel		
	Simplified I ² C	2 channels	3 channels	None		
DMA function		2 channels		None		
Safety function	CRC operation	Yes		None		
	RAM guard	Yes		None		
	SFR guard	Yes		None		

- 1.4 Pin Configuration (Top View)
- 1.4.1 20-pin products

• 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65 mm pitch)

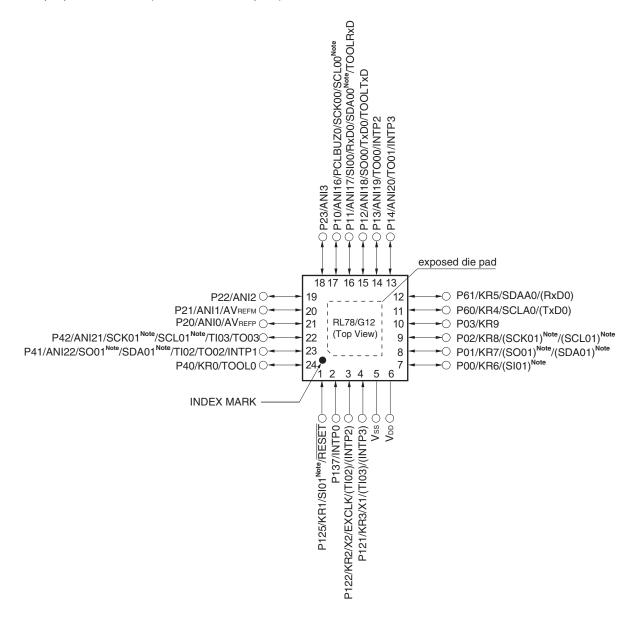


Note Provided only in the R5F102 products.

- Remarks 1. For pin identification, see 1.5 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).

1.4.2 24-pin products

<R> • 24-pin plastic HWQFN (4 × 4 mm, 0.5 mm pitch)

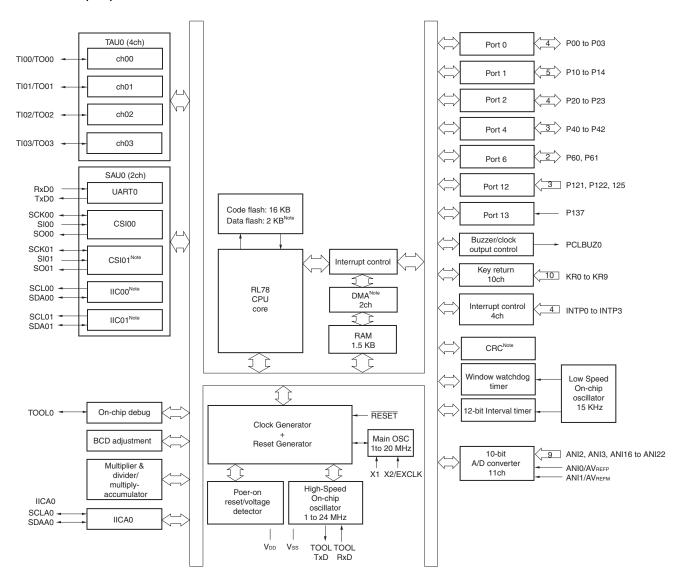


Note Provided only in the R5F102 products.

Remarks 1. For pin identification, see 1.5 Pin Identification.

- 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).
- 3. It is recommended to connect an exposed die pad to Vss.

1.6.2 24-pin products



Note Provided only in the R5F102 products.

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42		0.8Vpb		V _{DD}	V
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147					
	V _{IH2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	2.2		V _{DD}	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	2.0		V _{DD}	٧
		30-pin products: P01, P10, P11, P13 to P17	$1.8~V \leq V_{DD} < 3.3~V$	1.5		V _{DD}	V
	V _{IH3}	P20 to P23		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60, P61		0.7V _{DD}		6.0	V
	V _{IH5}	P121, P122, P125 ^{Note 1} , P137, I	0.8V _{DD}		V _{DD}	V	
Input voltage, low	V _{IL1}	Normal input buffer		0		0.2V _{DD}	V
		20-, 24-pin products: P00 to P0 P40 to P42					
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	V _{IL2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}$	0		0.5	٧
		30-pin products: P01, P10, P11, P13 to P17	$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}$	0		0.32	V
	V _{IL3}	P20 to P23		0		0.3V _{DD}	V
	VIL4	P60, P61		0		0.3V _{DD}	٧
	V _{IL5}	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2V _{DD}	٧
Output voltage, high	V он1	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	V _{DD} -1.5			V
		P40 to P42 30-pin products:	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -3.0 \text{ mA}$	V _{DD} -0.7			V
	P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120,	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} -0.6			٧	
		P147	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -1.5 \text{ mA}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Iон₂ = −100 μA	V _{DD} -0.5			V

Notes 1. 20, 24-pin products only.

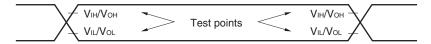
2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.5 Peripheral Functions Characteristics

AC Timing Test Point



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		h-speed Mode	,	/-speed Mode	Unit	
			MIN.	MAX.	MIN.	MAX.		
Transfer rate				fмск/6		fмск/6	bps	
Note 1		Theoretical value of the maximum transfer rate $f_{\text{CLK}} = f_{\text{MCK}}^{\text{Note2}}$		4.0		1.3	Mbps	

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

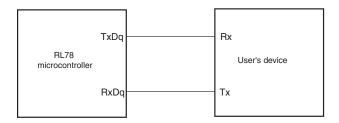
HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

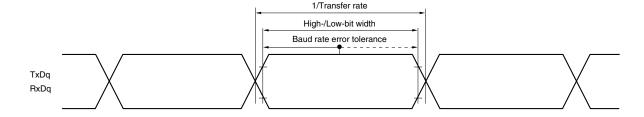
LS (low-speed main) mode: $8 \text{ MHz} (1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 2), g: PIM, POM number (g = 0, 1)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))

(2) During communication at same potential (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-sp	Unit	
			MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	tkCY1	tkcy1 ≥ 2/fclk	83.3		250		ns
SCK00 high-/low- level width	t кн1,	$4.0~V \leq V_{DD} \leq 5.5~V$	tkcy1/2-7		tkcy1/2-50		ns
	t KL1	$2.7~V \leq V_{DD} \leq 5.5~V$	tkcy1/2-10		tkcy1/2-50		ns
SI00 setup time	tsıĸı	$4.0~V \leq V_{DD} \leq 5.5~V$	23		110		ns
(to SCK00↑) Note 1		$2.7~V \leq V_{DD} \leq 5.5~V$	33		110		ns
SI00 hold time (from SCK00↑) Note2	tksi1		10		10		ns
Delay time from SCK00↓ to SO00 output Note 3	tkso1	C = 20 pF Note 4		10		10	ns

- **Notes 1.** When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 setup time becomes "to $SCK00\downarrow$ " when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - 2. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The SI00 hold time becomes "from SCK00↓" when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - 3. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1. The delay time to SO00 output becomes "from SCK00 \uparrow " when DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
 - 4. C is the load capacitance of the SCK00 and SO00 output lines.

Caution Select the normal input buffer for the SI00 pin and the normal output mode for the SO00 and SCK00 pins by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

Remarks 1. This specification is valid only when CSI00's peripheral I/O redirect function is not used.

 fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions		nigh-speed in) Mode		ow-speed n) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer		Reception	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$		fмск/6		fмск/6	bps
rate Note4			$2.7~V \leq V_b \leq 4.0~V$		Note1		Note1	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$		4.0		1.3	Mbps	
		$2.7 \text{ V} \le V_{DD} < 4.0 \text{ V},$		fмск/6		fмск/6	bps	
			$2.3~V \leq V_b \leq 2.7~V$		Note1		Note1	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note3}$		4.0		1.3	Mbps	
			$1.8 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$		fмск/6		fмск/6	bps
		$1.6~V \leq V_b \leq 2.0~V$		Notes1, 2		Notes1, 2		
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note3}$		4.0		1.3	Mbps
		Transmission	·		Note4		Note4	bps
			$2.7~V \leq V_b \leq 4.0~V$					
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 Note5		2.8 Note5	Mbps
			$2.7 \text{ V} \le V_{DD} < 4.0 \text{ V},$		Note6		Note6	bps
			$2.3~V \leq V_b \leq 2.7~V,$					
	$transfer \ r$ $C_b = 50 \ p$ $1.8 \ V \le V_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$ $Theoretic transfer \ r$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note7		1.2 Note7	Mbps	
			$1.8 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$		Notes		Notes	bps
			$1.6~V \leq V_b \leq 2.0~V$		2, 8		2, 8	
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note9		0.43 Note9	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with $V_{DD} \ge V_b$.
- 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V
$$\leq$$
 V_{DD} \leq 5.5 V)

LS (low-speed main) mode: $8 \text{ MHz} (1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

4. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\left\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\right\} \times 3} \quad \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{ln } (1 - \frac{2.2}{\text{Vb}})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(Ta = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high	h-speed Mode	LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	tkcy1	tkcy1 ≥ 2/fCLK	$\begin{aligned} &4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 20 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	200		1150		ns
			$\begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 20 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	300		1150		ns
SCK00 high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 50		tксү1/2— 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	$0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ = $2.7 \text{ k}\Omega$	tксу1/2 — 120		tксу1/2 – 120		ns
SCK00 low-level width	t _{KL1}	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.$ $C_{\text{b}} = 20 \text{ pF, R}_{\text{b}} =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 7		tксү1/2 – 50		ns
		$2.7~V \leq V_{DD} < 4.0~V,~2.3~V \leq V_b \leq 2.7~V,$ $C_b = 20~pF,~R_b = 2.7~k\Omega$		tксу1/2 — 10		tксү1/2 – 50		ns
SI00 setup time (to SCK00↑) Note 1	tsıĸ1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ Rb} =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω	58		479		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	121		479		ns
SI00 hold time (from SCK00↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF, R}_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		ns
Delay time from SCK00↓ to SO00 output Note 1	tkso1	$4.0 \text{ V} \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		60		60	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω		130		130	ns
SI00 setup time (to SCK00↓) Note 2	tsıĸı	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF, R}_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, $= 1.4 \ k\Omega$	23		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	33		110		ns
SI00 hold time (from SCK00↓) Note 2	tksi1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ R}_b =$	$5~V,~2.7~V \leq V_b \leq 4.0~V,$ = 1.4 k Ω	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	10		10		ns
Delay time from SCK00↑ to SO00 output Note 2	t _{KSO1}	$4.0~V \leq V_{DD} \leq 5.$ $C_b = 20~pF,~R_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω		10		10	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 k Ω		10		10	ns

(Notes, Caution, and Remarks are listed on the next page.)



- Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1
 - **2.** When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.
- Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (VDD tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1).

 For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** Rb [Ω]:Communication line (SCK00, SO00) pull-up resistance, Cb [F]: Communication line (SCK00, SO00) load capacitance, Vb [V]: Communication line voltage
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode	
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp [↑]) Note 1	tsıĸı	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	81		479		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, $ $ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega $	177		479		ns
		$ \begin{cases} 1.8 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V^{\text{Note 2}}, \\ C_{b} = 30 \ pF, \ R_{b} = 5.5 \ k\Omega \end{cases} $	479		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$ 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, $ $ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega $	19		19		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, $ $ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega $	19		19		ns
		$\begin{split} 1.8 \ V & \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b & = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	19		19		ns
Delay time from t SCKp↓ to SOp output Note 1	tkso1	$ 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, $ $ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega $		100		100	ns
		$2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V,$ $C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega$		195		195	ns
		$ \begin{aligned} &1.8 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $		483		483	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with $V_{DD} \ge V_b$.

(Cautions and Remarks are listed on the next page.)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel		Reference Voltage	
	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM
ANI0 to ANI3	Refer to 28.6.1 (1).	Refer to 28.6.1 (3).	Refer to 28.6.1 (4).
ANI16 to ANI22	Refer to 28.6.1 (2).		
Internal reference voltage Temperature sensor	Refer to 28.6.1 (1).		_
output voltage			

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.8 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±3.5	LSB
		AVREFP = VDD Note 3			1.2	±7.0 Note 4	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI3	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
				57		95	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
	output voltage	output voltage (HS (high-speed main)					
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution				±0.25	%FSR
		AVREFP = VDD Note 3				$\pm 0.50^{\text{Note 4}}$	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution				±0.25	%FSR
		AVREFP = VDD Note 3				$\pm 0.50^{\text{Note 4}}$	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±2.5	LSB
		AVREFP = VDD Note 3				±5.0 Note 4	LSB
Differential linearity error	DLE	10-bit resolution				±1.5	LSB
Note 1		AVREFP = VDD Note 3				±2.0 Note 4	LSB
Analog input voltage	VAIN	ANI2, ANI3		0		AVREFP	V
		Internal reference voltage (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) m			VBGR Note 5		V
		Temperature sensor outp (2.4 V \leq VDD \leq 5.5 V, HS	out voltage (high-speed main) mode)		VTMPS25 Note !	5	V

(Notes are listed on the next page.)



 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

(4/4)

Parameter	Symbol		Conditio	ns	MIN.	TYP.	MAX.	Unit
Output voltage, low	V _{OL1}	P00 to P03 ^{Note} , P10 to P14, P40 to P42 2. 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
				$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.6	V
				$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
				$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 0.6 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P23		Ιοι2 = 400 μΑ			0.4	V
	Vol3	P60, P61		$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 15.0~mA$			2.0	V
				$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 5.0 \text{ mA}$			0.4	V
				$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.4	V
				$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 2.0 \text{ mA}$			0.4	V
Input leakage current, high	Ішн1	Other than P121, P122	$V_{I} = V_{DD}$				1	μА
	ILIH2	P121, P122 (X1, X2/EXCLK)	VI = VDD	Input port or external clock input			1	μА
				When resonator connected			10	μΑ
Input leakage current, low	ILIL1	Other than P121, P122	Vı = Vss				-1	μΑ
	ILIL2	P121, P122 (X1, X2/EXCLK)	Vı = Vss	Input port or external clock input			-1	μΑ
				When resonator connected			-10	μΑ
On-chip pull-up resistance	Ru	20-, 24-pin product P00 to P03 ^{Note} , P10 P40 to P42, P125,) to P14,	V _I = V _{SS} , input port	10	20	100	kΩ
		30-pin products: P0 P10 to P17, P30, F P50, P51, P120, P	P31, P40,					

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

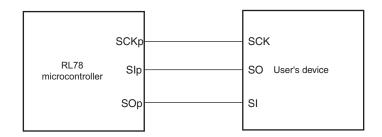
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	mbol Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note4	tkcy2	tkcy2 4.0 V ≤ V _{DD} ≤ 5.5 V	20 MHz < fmck	16/fмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	16/fмск		ns
			fмcк ≤ 16 MHz	12/fмск		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		12/fмск		ns
				and 1000		
SCKp high-/low-level width	t кн2,	$4.0~V \leq V_{DD} \leq 5.5~V$		tксү2/2-14		ns
	t _{KL2}	$2.7~V \leq V_{DD} \leq 5.5~V$		tксү2/2–16		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		tксү2/2-36		ns
SIp setup time (to SCKp↑)	tsik2	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		1/fмск + 40		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		1/fмск + 60		ns
Slp hold time (from SCKp [↑]) Note 2	t _{KSI2}			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note4	$2.7~V \leq V_{DD} \leq 5.5~V$		2/fмcк + 66	ns
			$2.4~V \leq V_{DD} \leq 5.5~V$		2/fмcк + 113	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp \uparrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

CSI mode connection diagram (during communication at same potential)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	HS (high-speed main) Mode	
			MIN.	MAX.	
SIp setup time (to SCKp [↑])	tsıkı	$ \begin{aligned} 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	162		ns
		$ \label{eq:continuous} $	354		ns
		$ \label{eq:continuous} $	958		ns
SIp hold time (from SCKp↑) Note	tksii	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	38		ns
		$ \label{eq:continuous} $	38		ns
		$\label{eq:controller} \begin{array}{c} 2.4 \; V \leq V_{DD} < 3.3 \; V, \; 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	38		ns
Delay time from SCKp↓ to SOp output Note	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $		200	ns	
		$ \label{eq:continuous} $		390	ns
				966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

($\pmb{\mathsf{Cautions}}$ and $\pmb{\mathsf{Remarks}}$ are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-sր Mo	•	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$		100 ^{Note1}	kHz
				100 ^{Note1}	kHz
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$		100 ^{Note1}	kHz
Hold time when SCLr = "L"	tLOW	$\begin{aligned} &C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \\ &4.0 \ V \leq V_{DD} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ &C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned}$	4600		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega $	4600		ns
		$ \label{eq:continuous} $	4650		ns
Hold time when SCLr = "H"	thigh	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	2700		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega $	2400		ns
			1830		ns
Data setup time (reception)	tsu:dat	$ 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, $ $ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega $	1/fмск + 760 Note3		ns
			1/f _{MCK} + 760 Note3		ns
		$2.4~V \leq V_{DD} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V,$ $C_b = 100~pF,~R_b = 5.5~k\Omega$	1/f _{MCK} + 570 Note3		ns
Data hold time (transmission)	thd:dat	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	0	1420	ns
			0	1420	ns
		$\label{eq:continuous} $2.4 \ V \le V_{DD} < 3.3 \ V, \ 1.6 \ V \le V_{b} \le 2.0 \ V,$$$$$$$$C_{b} = 100 \ pF, \ R_{b} = 5.5 \ k\Omega$$$	0	1215	ns

Notes 1. The value must also be equal to or less than fmck/4.

2. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Cautions 1. Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

2. IIC01 and IIC11 cannot communicate at different potential.

(Remarks are listed on the next page.)



- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to 29.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3			1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin: ANI16 to ANI22	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error Notes 1, 2	EZS	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.35	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AV _{REFP} = V _{DD} Note 3				±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD Note 3				±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD Note 3				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI22		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM (ADREFM = 1), target pin: ANI0, ANI2, ANI3, and ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		VBGR Note 3	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 29.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AV_{REFM}.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AV_{REFM}.

Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

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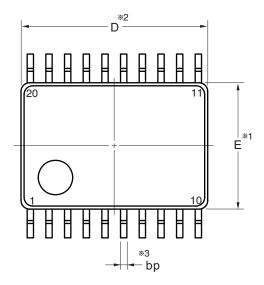
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4. PACKAGE DRAWINGS

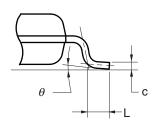
4.1 20-pin products

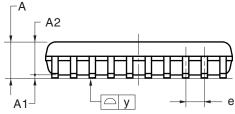
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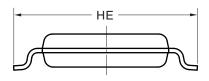
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end







NOTE

- 1.Dimensions "X1" and "X2" do not include mold flash.
- 2.Dimension "X3" does not include trim offset.

	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	$0.22 + 0.10 \\ -0.05$
С	$0.15 + 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

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